

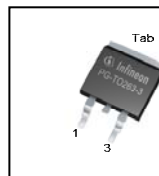
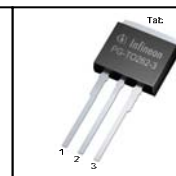
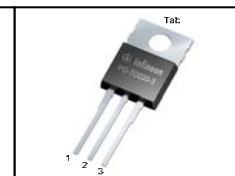
OptiMOS[®] -T2 Power-Transistor

Product Summary

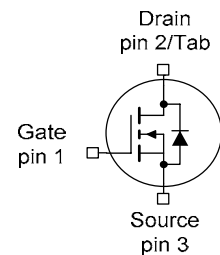
V_{DS}	60	V
$R_{DS(on),max}$ (SMD version)	5.4	m Ω
I_D	80	A

Features

- N-channel - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested

PG-TO263-3-2

PG-TO262-3-1

PG-TO220-3-1


Type	Package	Marking
IPB80N06S4-05	PG-TO263-3-2	4N0605
IPI80N06S4-05	PG-TO262-3-1	4N0605
IPP80N06S4-05	PG-TO220-3-1	4N0605


Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25^\circ\text{C}, V_{GS}=10\text{V}^{(1)}$	80	A
		$T_C=100^\circ\text{C}, V_{GS}=10\text{V}^{(2)}$	75	
Pulsed drain current ⁽²⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	320	
Avalanche energy, single pulse ⁽²⁾	E_{AS}	$I_D=40\text{A}$	152	mJ
Avalanche current, single pulse	I_{AS}	-	80	A
Gate source voltage	V_{GS}	-	± 20	V
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	107	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics²⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.4	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1\text{mA}$	60	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=60\mu\text{A}$	2.0	3.0	4.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	0.01	1	μA
		$V_{DS}=60V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	5	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=80\text{A}$	-	4.7	5.7	m Ω
		$V_{GS}=10V, I_D=80\text{A}, \text{SMD version}$	-	4.4	5.4	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	5000	6500	pF
Output capacitance	C_{oss}		-	1230	1600	
Reverse transfer capacitance	C_{rss}		-	50	100	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30V, V_{GS}=10V,$ $I_D=80A, R_G=3.5\Omega$	-	20	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	35	-	
Fall time	t_f		-	8	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=48V, I_D=80A,$ $V_{GS}=0$ to 10V	-	28	36	nC
Gate to drain charge	Q_{gd}		-	7	14	
Gate charge total	Q_g		-	62	81	
Gate plateau voltage	$V_{plateau}$		-	5.6	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ C$	-	-	80	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	320	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=80A,$ $T_j=25^\circ C$	0.6	0.95	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=30V, I_F=80A,$ $di_F/dt=100A/\mu s$	-	36	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	41	-	

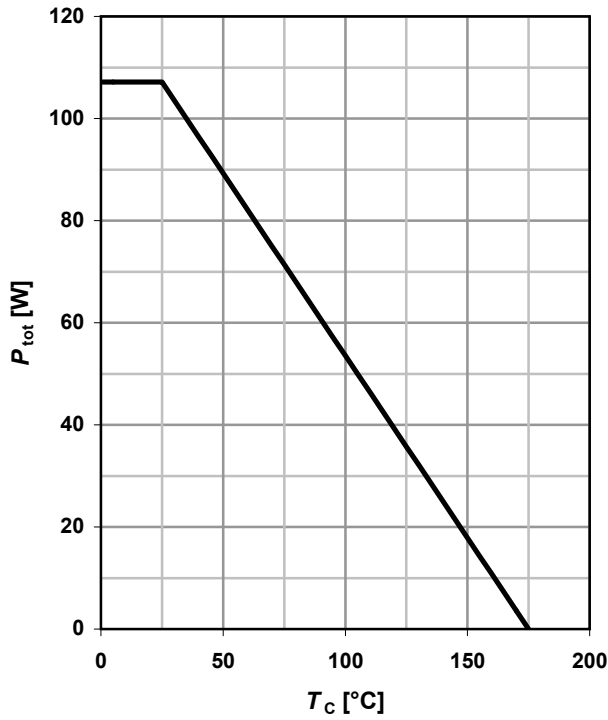
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 1.4K/W$ the chip is able to carry 106A at 25°C.

²⁾ Specified by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

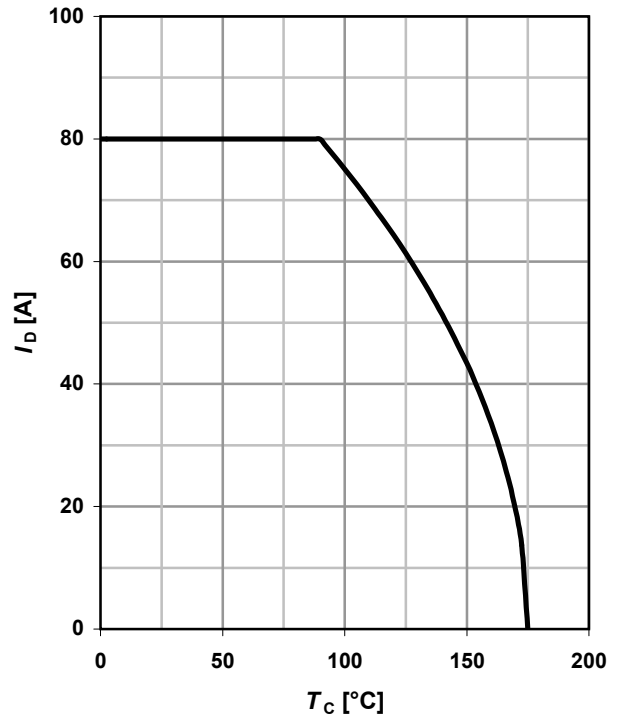
1 Power dissipation

$P_{tot} = f(T_C); V_{GS} \geq 6 V$



2 Drain current

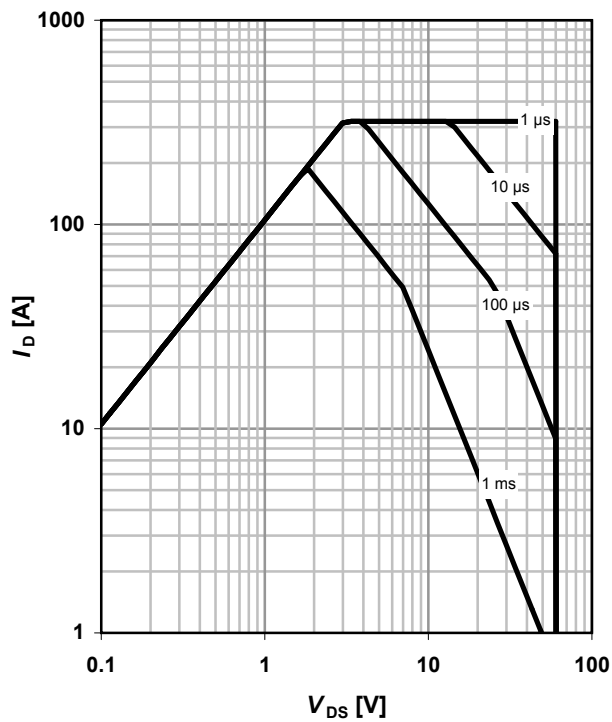
$I_D = f(T_C); V_{GS} \geq 6 V; SMD$



3 Safe operating area

$I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0; SMD$

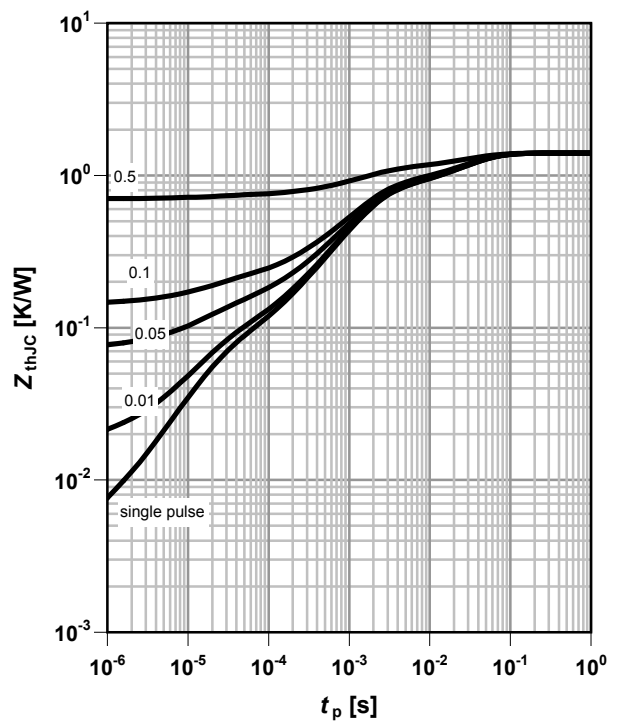
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

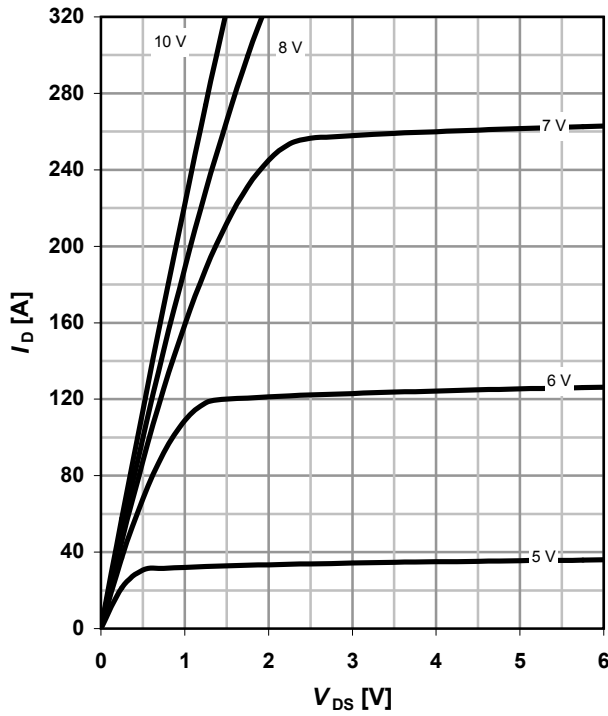
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ °C}; \text{SMD}$

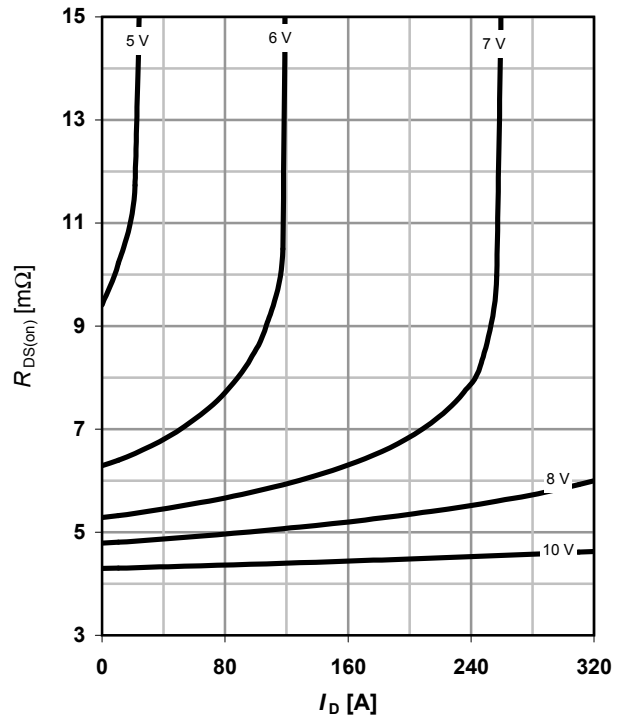
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}; \text{SMD}$

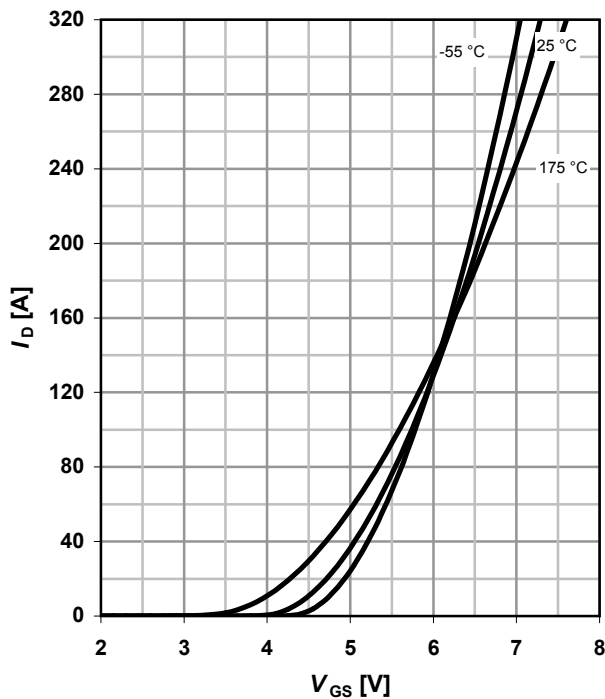
parameter: V_{GS}



7 Typ. transfer characteristics

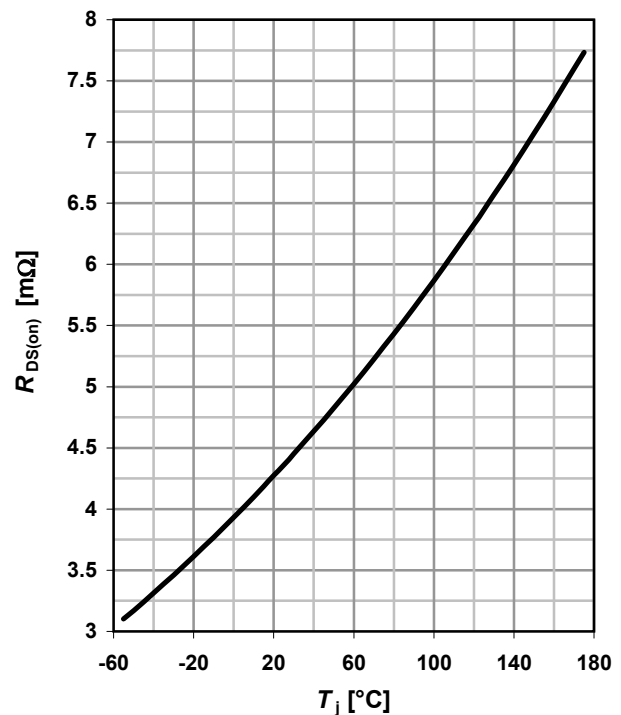
$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter: T_j



8 Typ. drain-source on-state resistance

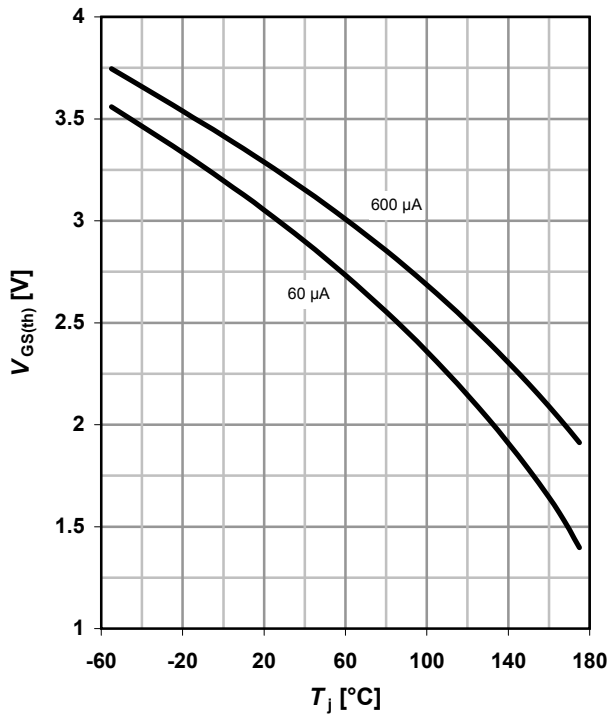
$R_{DS(on)} = f(T_j); I_D = 80\text{ A}; V_{GS} = 10\text{ V}; \text{SMD}$



9 Typ. gate threshold voltage

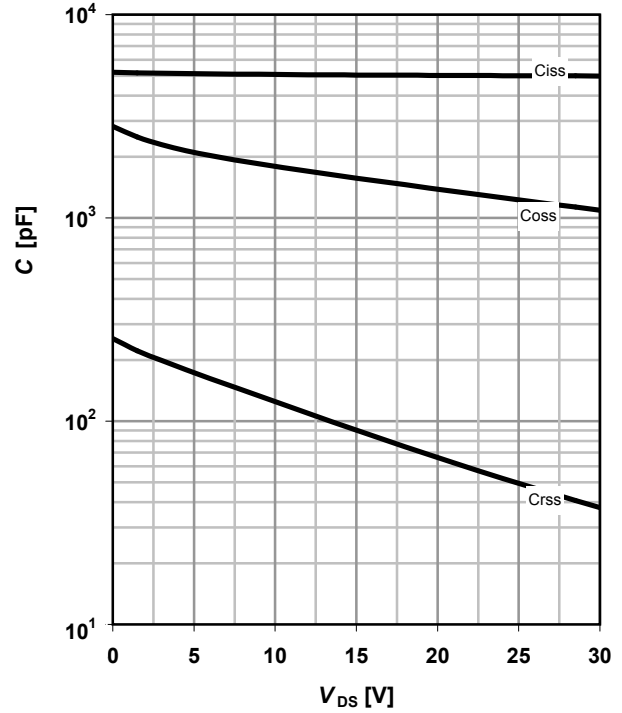
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

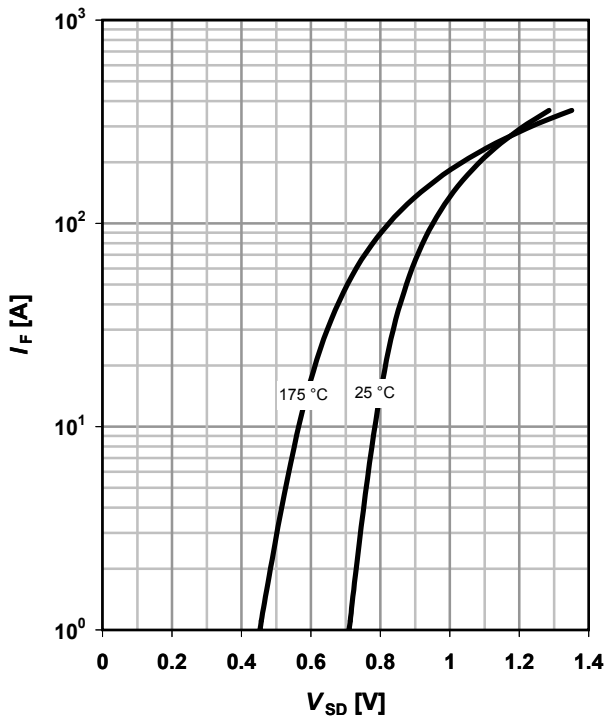
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

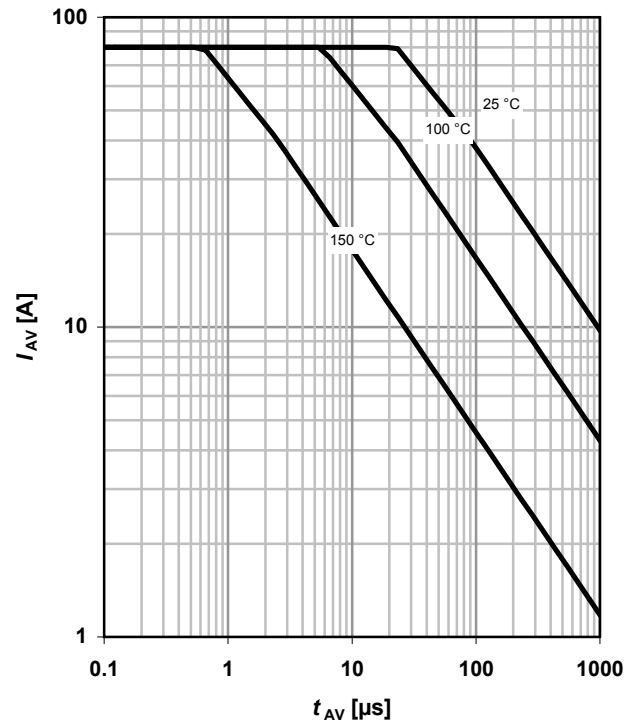
parameter: T_j



12 Avalanche characteristics

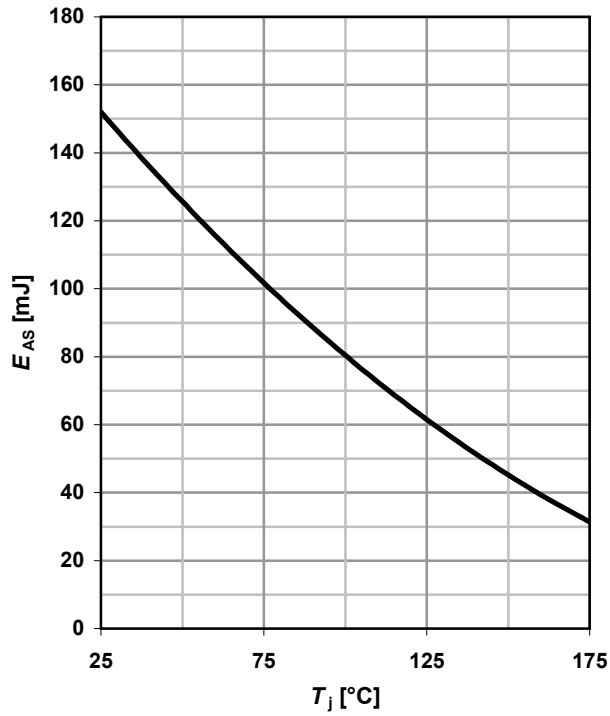
$I_{AS} = f(t_{AV})$

parameter: $T_{j(start)}$



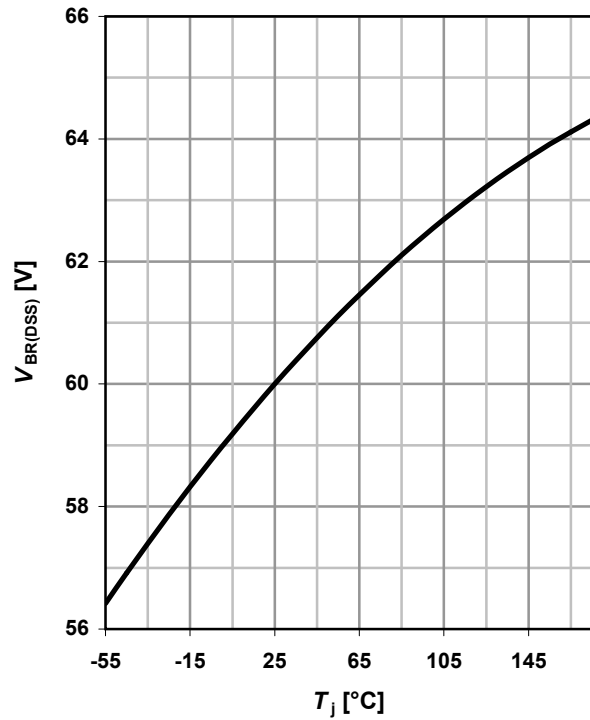
13 Avalanche energy

$E_{AS} = f(T_j); I_D = 40 \text{ A}$



14 Drain-source breakdown voltage

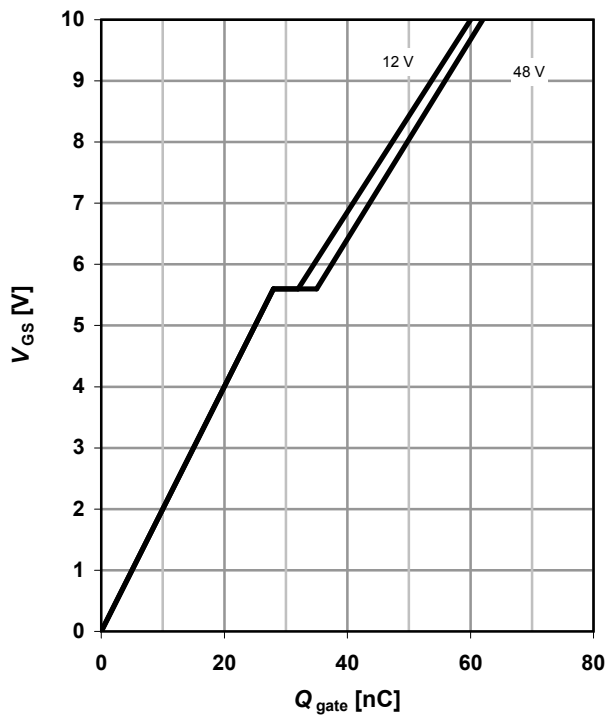
$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$



15 Typ. gate charge

$V_{GS} = f(Q_{gate}); I_D = 80 \text{ A pulsed}$

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

Version	Date	Changes
Revision 1.0	24.03.2009	Final data sheet